

AN2009-02

Stacks with IGBT modules

The Use of Snubber Capacitors in Stacks
with IGBT modules

IFAG OP ATP HPS SO STA D



Never stop thinking

Edition 2009-06-05

**Published by
Infineon Technologies AG
59568 Warstein, Germany**

**© Infineon Technologies AG 2009.
All Rights Reserved.**

LEGAL DISCLAIMER

THE INFORMATION GIVEN IN THIS APPLICATION NOTE IS GIVEN AS A HINT FOR THE IMPLEMENTATION OF THE INFINEON TECHNOLOGIES COMPONENT ONLY AND SHALL NOT BE REGARDED AS ANY DESCRIPTION OR WARRANTY OF A CERTAIN FUNCTIONALITY, CONDITION OR QUALITY OF THE INFINEON TECHNOLOGIES COMPONENT. THE RECIPIENT OF THIS APPLICATION NOTE MUST VERIFY ANY FUNCTION DESCRIBED HEREIN IN THE REAL APPLICATION. INFINEON TECHNOLOGIES HEREBY DISCLAIMS ANY AND ALL WARRANTIES AND LIABILITIES OF ANY KIND (INCLUDING WITHOUT LIMITATION WARRANTIES OF NON-INFRINGEMENT OF INTELLECTUAL PROPERTY RIGHTS OF ANY THIRD PARTY) WITH RESPECT TO ANY AND ALL INFORMATION GIVEN IN THIS APPLICATION NOTE.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

AN2009-02

Revision History:	2009-05	V1.1
Previous Version:	none	


<p>We Listen to Your Comments</p> <p>Any information within this document that you feel is wrong, unclear or missing at all? Your feedback will help us to continuously improve the quality of this document. Please send your proposal (including a reference to this document) to:</p> <p>IGBT.application@infineon.com</p>	
---	---

Table of Contents		Page
1	Intention of this Application Note	5
2	Influence of Stray Inductance	5
3	The Funktion of a Snubber Capacitor	5
4	Usage of Snubber Capacitors	6
4.1	Advantages vs. Disadvantages	6
4.2	Determining the Technical Parameters of the Snubber Capacitor	7
4.2.1	Temperatur	7
4.2.2	Capacitance	7
4.2.3	Current Carrying Capability	7

1 Intention of this Application Note

Snubber capacitors are used to reduce the overvoltages at the IGBTs during switching instances. They can simplify the design of the stack as the effect of the parasitic DC-link inductances L_{σ} is reduced. The intention of this application note is to give the user background knowledge about the necessity and selection of snubbers.

2 Influence of Stray Inductance

Inductances of issues are especially the DC-link inductance L_{σ} which is mainly caused by the mechanical design and the inductance of the DC-link capacitors.

When an IGBT is turned off the collector current drops with a given di/dt . The di/dt in conjunction with L_{σ} causes an induced voltage which is added to the DC-link voltage as depicted in figure 1. Thus the IGBT has to withstand a voltage of

$$V_{CE} = V_{DC} + V_{\sigma} = V_{DC} + L_{\sigma} \cdot di/dt,$$

where V_{DC} represents the DC-link voltage

Especially during short circuit turn off, when high values of di/dt occur or in case of high DC-link voltages it is getting critical to the IGBT regarding its blocking voltage capability.

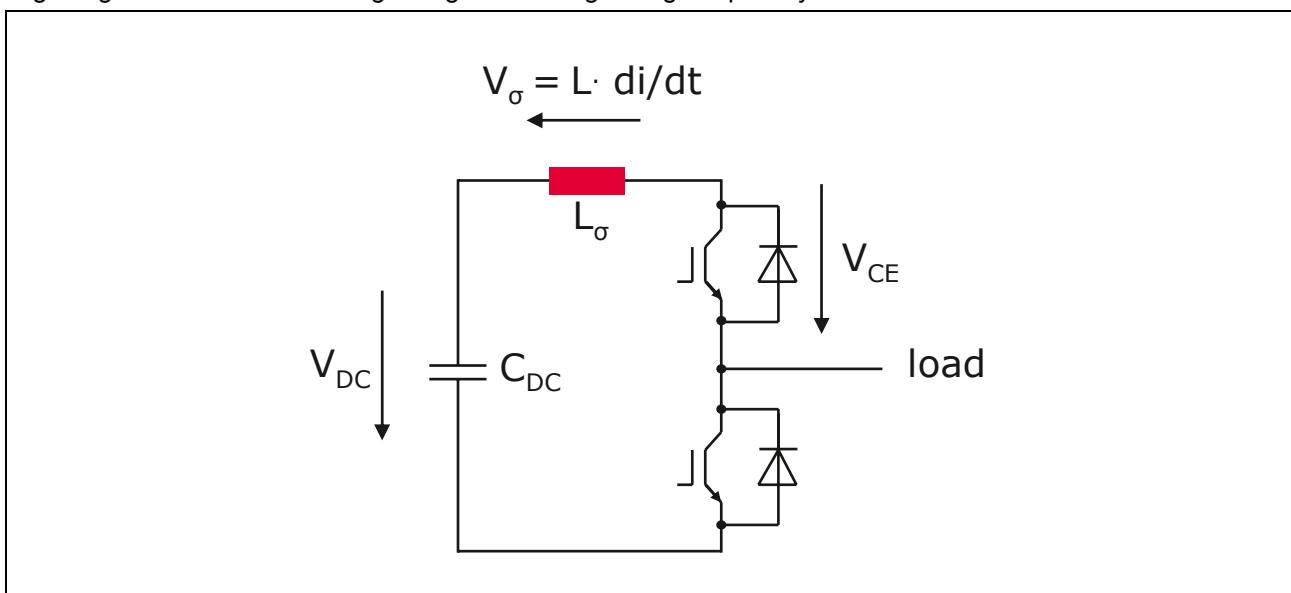


Figure 1 Stray inductance in commutation circuit

3 The Funktion of a Snubber Capacitor

The snubber capacitor partly compensates the effect of the stray inductances L_{σ} within the commutation circuit. As the capacitor voltage can not change its value immediately, a current is necessary to change it:

$$I_{\text{capacitor}} = C \cdot du/dt$$

Thus the V_{σ} , forced by L_{σ} can not appear at the IGBT like calculated above. First the snubber has to be charged. Additionally the snubber acts as a separator of the stray inductance. L_{σ} is divided into $L_{\sigma 1}$ and $L_{\sigma 2}$ (refer to figure 2). Now only $L_{\sigma 2}$ is relevant for the IGBT. As $L_{\sigma 2} < L_{\sigma}$, the over voltage is reduced.

The closer the snubber is mounted to the IGBT mechanically, the more the over voltage is reduced during switching. Thus it is typically recommended to mount the snubber as close as possible to the IGBT modules.

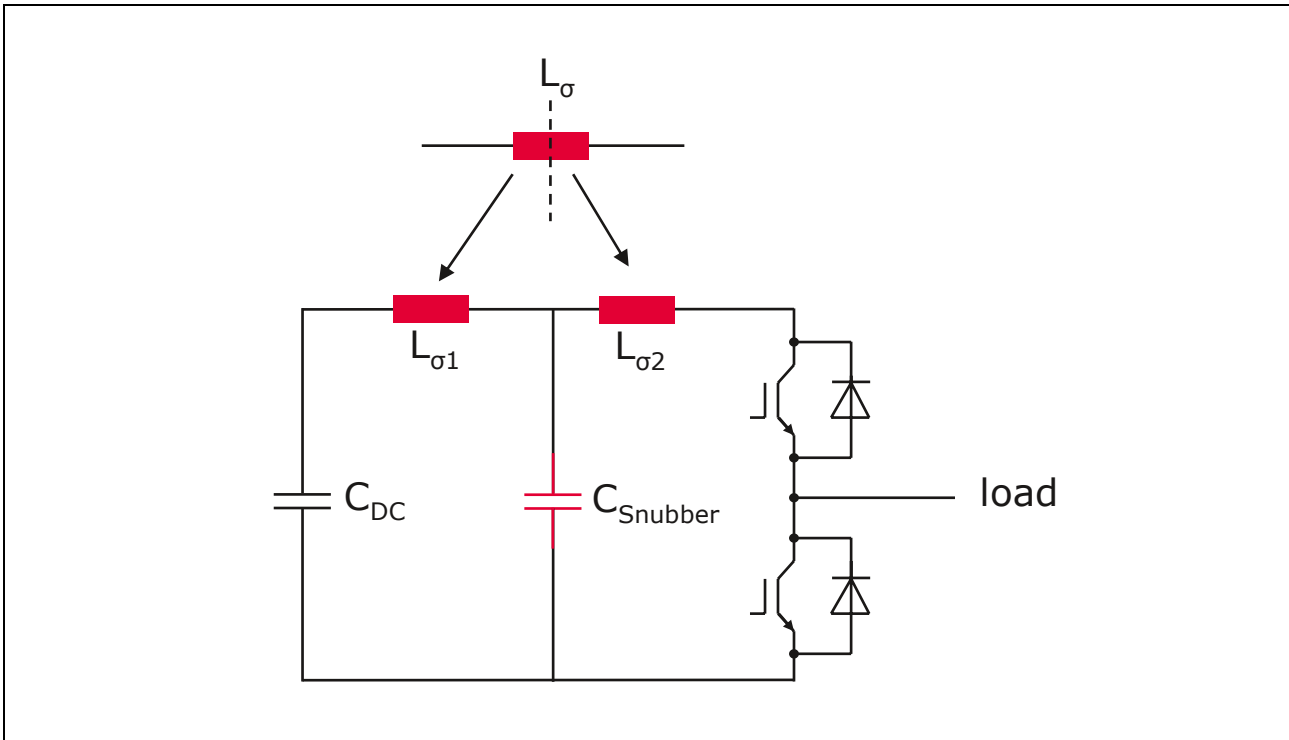


Figure 2 Adding a snubber capacitor into the commutation circuit

4 Usage of Snubber Capacitors

The snubber capacitors can reduce overvoltages and help to protect the IGBT in critical situations.

4.1 Advantages vs. Disadvantages

Especially if DC-links with electrolytic capacitors are used snubbers are absolutely recommended. The high level of inherent inductance of electrolytic capacitors compared with its typical series connection which multiplies this value is quite dangerous to the IGBT if its blocking capability is exceeded.

In this case the snubber capacitor fulfills the function of over voltage reduction.

On the other hand snubber capacitors have some disadvantages:

- Additional parts with additional FIT-rates
- Additional costs
- Additional mounting space
- Specific life time, depending on application parameters, mainly load current and switching frequency
- Maximum allowed parameters given by the capacitors specification limit the use in larger power stacks:
 - the allowed RMS snubber current results in a limitation
 - the allowed temperatures could be exceeded due to high temperatures at or near the main terminals of power modules, especially modules with $T_{vj} = 150^{\circ}\text{C}$ like PrimePACK™

4.2 Determining the Technical Parameters of the Snubber Capacitor

Like DC-link capacitors, snubber capacitors need to be especially designed and selected for each application respectively for each stack. The following sections explain the most critical parameters for choosing the right snubber.

4.2.1 Temperatur

Two temperatures should be taken into account when selecting a snubber:

- Ambient temperature
- Core temperature

The ambient temperature relates to the direct ambient around each snubber. This is typically not the ambient temperature around the stack. The ambient temperature is supposed to be evaluated experimentally.

The core temperature on the one hand is a consequence of the snubber losses, driven by its RMS current and the parasitic resistor in combination with the thermal resistance. On the other hand the snubber is typically mounted near the module. As the module's main terminals can be heated by the module's losses to up to $>100^{\circ}\text{C}$, especially for modules driven with $T_{vj} = 150^{\circ}\text{C}$, the snubbers core temperature is mainly influenced by it. The core temperature is also supposed to be evaluated experimentally.

4.2.2 Capacitance

The electrical capacitance the snubber should have depends on both the stray inductance of the commutation circuit L_{σ} and the di/dt of the commutating current. The larger L_{σ} and/or the di/dt the higher the required value of the snubbers capacitance. The following ranges of C_{Snubber} per module are recommended:

- | | |
|--------------------|-------------------------|
| • 62mm module | 0,2...0,5 μF |
| • IHM module | 0,8...1,2 μF |
| • PrimePACK module | 1,2...1,5 μF |

4.2.3 Current Carrying Capability

The needed current carrying capability of each snubber capacitor does mainly depend on

- RMS output current of the IGBT module(s) the snubber relates to
- Switching frequency of the IGBT
- Switching behaviour of the IGBT
- Stray inductance L_{σ} of the DC-link
- Capacitance of the snubber

Figure 3 shows the principle behaviour of the RMS snubber current depending on the modules RMS current and its switching frequency.

→ The higher the RMS-output current of the IGBT the higher the snubber current

→ The higher the switching frequency the higher the snubber current

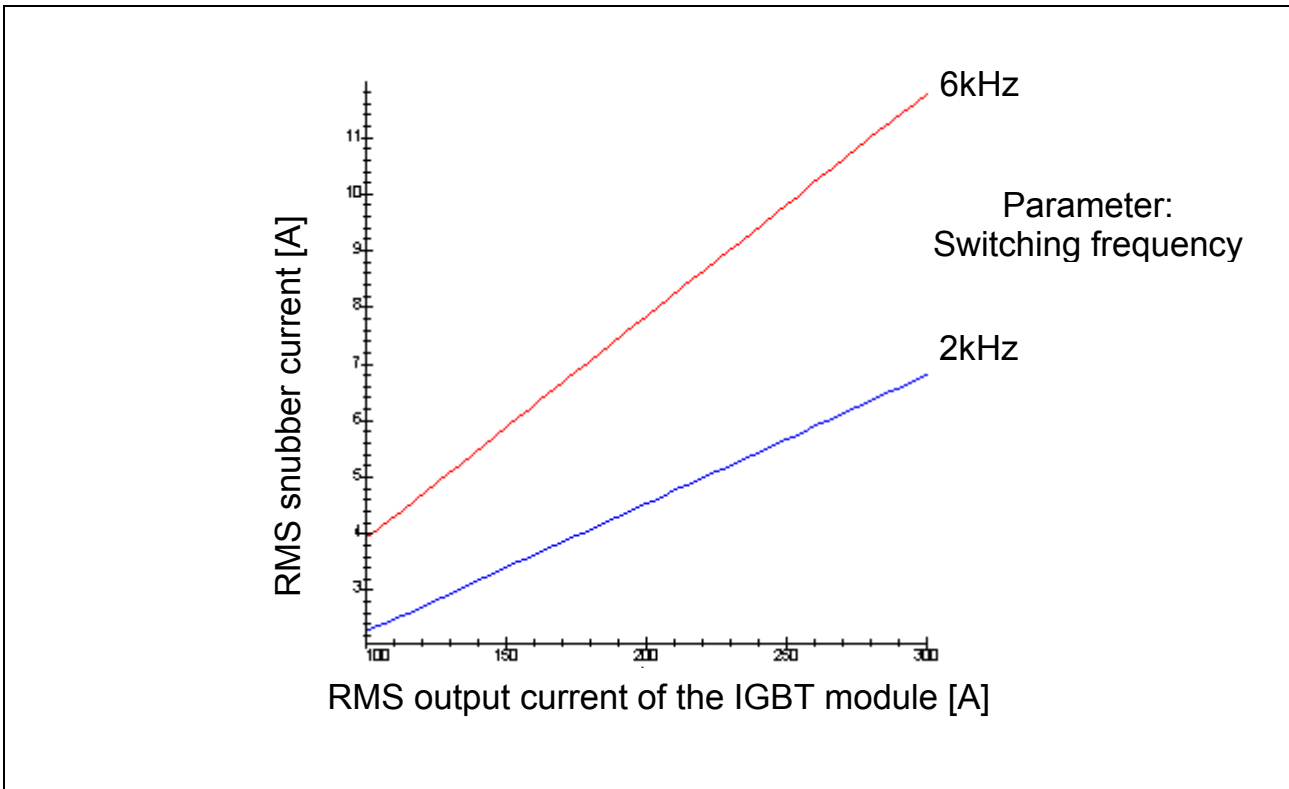


Figure 3 Influence of switching frequency and output current on the snubber current

Note: Figure 3 shows just one example for one special stack in one special application. Thus it doesn't need to be valid for any other stacks and applications. However, the theoretical dependency as shown is valid for any application and stack.

<http://www.infineon.com>